

Hitoshi Habuka

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

146
papers

1,106
citations

16
h-index

24
g-index

156
ext. papers

1,215
ext. citations

1.9
avg, IF

4.14
L-index

#	Paper	IF	Citations
146	Anticorrosive Behavior of Aluminum Nitride Surface Exposed to Chlorine Trifluoride Gas at High Temperatures. <i>ECS Journal of Solid State Science and Technology</i> , 2021 , 10, 034006	2	
145	Boron-Silicon Film Chemical Vapor Deposition Using Boron Trichloride, Dichlorosilane and Monomethylsilane Gases. <i>ECS Journal of Solid State Science and Technology</i> , 2021 , 10, 064006	2	1
144	Benzoxazine-modified BMI Heat-resistant Resin with Low Dielectric Properties. <i>Transactions of the Japan Institute of Electronics Packaging</i> , 2021 , 14, E20-016-1-E20-016-14	0.3	0
143	Non-Plasma Dry Etcher Design for 200 mm-Diameter Silicon Carbide Wafer. <i>Materials Science Forum</i> , 2020 , 1004, 167-172	0.4	0
142	Etching Rate Profile of C-Face 4H-SiC Wafer Depending on Total Gas Flow Rate of Chlorine Trifluoride and Nitrogen. <i>Materials Science Forum</i> , 2020 , 1004, 173-179	0.4	1
141	Development of SiC Etching by Chlorine Fluoride Gas. <i>Materials Science Forum</i> , 2020 , 1004, 731-737	0.4	1
140	SiC Epitaxial Reactor Cleaning by ClF ₃ Gas with the Help of Reaction Heat. <i>Materials Science Forum</i> , 2020 , 1004, 186-192	0.4	
139	Side wall water outlet design for silicon wafer wet cleaning bath. <i>Materials Science in Semiconductor Processing</i> , 2020 , 110, 104970	4.3	0
138	Electric Current in Rate Equation for Parallel Plate Plasma-Enhanced Chemical Vapour Deposition of SiC _x N _y O _z Film without Heat Assistance. <i>ECS Journal of Solid State Science and Technology</i> , 2020 , 9, 024017	2	0
137	Anticorrosive Behavior of SiC _x N _y O _z Film Formed by Non-Heat Assistance Plasma-Enhanced Chemical Vapor Deposition Using Monomethylsilane, Nitrogen and Argon Gases. <i>ECS Journal of Solid State Science and Technology</i> , 2020 , 9, 024001	2	1
136	Temperature Influence on Organic Molecular Interaction on Silicon Oxide Surface In Situ Measured Utilizing a Quartz Crystal Microbalance. <i>ECS Journal of Solid State Science and Technology</i> , 2020 , 9, 104007	2	1
135	Design of a Silicon Carbide Chemical Vapor Deposition Reactor Cleaning Process Using Chlorine Trifluoride Gas Accounting for Exothermic Reaction Heat. <i>ECS Journal of Solid State Science and Technology</i> , 2020 , 9, 104008	2	1
134	Deposition and etching behaviour of boron trichloride gas at silicon surface. <i>Journal of Crystal Growth</i> , 2020 , 529, 125301	1.6	4
133	Quartz crystal microbalance for real-time monitoring chlorosilane gas transport in slim vertical cold wall chemical vapor deposition reactor. <i>Materials Science in Semiconductor Processing</i> , 2020 , 106, 104759	4.3	1
132	Exposure of Tantalum Carbide, Silicon Nitride and Aluminum Nitride to Chlorine Trifluoride Gas. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, P175-P179	2	5
131	High-Temperature Reactor Cleaning Using Chlorine Trifluoride Gas for Silicon Carbide Chemical Vapor Deposition. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, P400-P406	2	3
130	Influence of Metal and Polymer Substrate on SiC _x N _y O _z Film Formation by Non-Heat Assistance Plasma-Enhanced Chemical Vapor Deposition Using Monomethylsilane, Nitrogen and Argon Gases. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, P407-P411	2	2

129	Behavior of Viscous Liquid Byproduct Formed in Exhaust Tube by Silicon Carbide Epitaxial Growth. <i>ECS Journal of Solid State Science and Technology</i> , 2019 , 8, P805-P810	2	0
128	High Temperature SiC Reactor Cleaning Using Chlorine Trifluoride Gas Achieved by Purified Pyrolytic Carbon Coating Film. <i>Materials Science Forum</i> , 2019 , 963, 141-145	0.4	1
127	Chlorine Trifluoride Gas Distributor Design for Single-Crystalline C-Face 4H-Silicon Carbide Wafer Etcher. <i>Materials Science Forum</i> , 2019 , 963, 520-524	0.4	2
126	Silicon epitaxial growth accelerated by parallel Langmuir processes using SiH ₂ Cl ₂ and SiH ₃ CH ₃ gases. <i>Semiconductor Science and Technology</i> , 2018 , 33, 094002	1.8	1
125	Advantages of a slim vertical gas channel at high SiHCl ₃ concentrations for atmospheric pressure silicon epitaxial growth. <i>Materials Science in Semiconductor Processing</i> , 2018 , 87, 13-18	4.3	4
124	Yttrium oxide film for protecting quartz glass surface from etching by long-term exposure to chlorine trifluoride gas at room temperature. <i>Materials Science in Semiconductor Processing</i> , 2018 , 83, 211-215	4.3	3
123	Quick and Practical Cleaning Process for Silicon Carbide Epitaxial Reactor. <i>Materials Science Forum</i> , 2018 , 924, 96-99	0.4	
122	Real time evaluation of silicon epitaxial growth process by exhaust gas measurement using quartz crystal microbalance. <i>Materials Science in Semiconductor Processing</i> , 2018 , 88, 192-197	4.3	5
121	4H-Silicon Carbide Wafer Surface after Chlorine Trifluoride Gas Etching. <i>Materials Science Forum</i> , 2018 , 924, 369-372	0.4	1
120	Water Outlet Design of Wet Cleaning Bath for 300-mm Diameter Silicon Wafers. <i>ECS Journal of Solid State Science and Technology</i> , 2018 , 7, N123-N127	2	1
119	Increase in silicon film deposition rate in a SiHCl ₃ -SiH _x -H ₂ system. <i>Journal of Crystal Growth</i> , 2017 , 468, 204-207	1.6	6
118	A Method to Adjust Polycrystalline Silicon Carbide Etching Rate Profile by Chlorine Trifluoride Gas. <i>Materials Science Forum</i> , 2017 , 897, 383-386	0.4	5
117	Susceptor Coating Materials Applicable for SiC Reactor Cleaning. <i>Materials Science Forum</i> , 2017 , 897, 99-102	0.4	8
116	Transport phenomena in a slim vertical atmospheric pressure chemical vapor deposition reactor utilizing natural convection. <i>Materials Science in Semiconductor Processing</i> , 2017 , 71, 348-351	4.3	5
115	Parallel langmuir processes for silicon epitaxial growth in a SiHCl ₃ -SiH _x -H ₂ system. <i>Materials Science in Semiconductor Processing</i> , 2017 , 72, 134-138	4.3	5
114	Non-Heat Assistance Plasma-Enhanced Chemical Vapor Deposition of SiC _x N _y O _z Film Using Monomethylsilane, Nitrogen and Argon. <i>ECS Journal of Solid State Science and Technology</i> , 2017 , 6, P443-P448	2	4
113	Mirror Etching of Single Crystalline C-Face 4H-Silicon Carbide Wafer by Chlorine Trifluoride Gas. <i>ECS Journal of Solid State Science and Technology</i> , 2017 , 6, P582-P585	2	6
112	Quick Cleaning Process for Silicon Carbide Chemical Vapor Deposition Reactor. <i>ECS Journal of Solid State Science and Technology</i> , 2017 , 6, P526-P530	2	11

111	Formation and Removal of Carbon Film on Silicon Carbide Surface Using Chlorine Trifluoride Gas. <i>ECS Journal of Solid State Science and Technology</i> , 2016 , 5, P441-P445	2	3
110	Repetition of In Situ Cleaning Using Chlorine Trifluoride Gas for Silicon Carbide Epitaxial Reactor. <i>ECS Journal of Solid State Science and Technology</i> , 2016 , 5, P12-P15	2	12
109	Non-heat assistance chemical vapor deposition of amorphous silicon carbide using monomethylsilane gas under argon plasma. <i>Surface and Coatings Technology</i> , 2016 , 285, 255-261	4.4	7
108	Slim Water Injection Nozzle for Silicon Wafer Wet Cleaning Bath. <i>Advances in Chemical Engineering and Science</i> , 2016 , 06, 345-354	0.4	4
107	Reflector Influence on Rapid Heating of Minimal Manufacturing Chemical Vapor Deposition Reactor. <i>ECS Journal of Solid State Science and Technology</i> , 2016 , 5, P280-P284	2	5
106	In Situ Measurement for Evaluating Temperature Change Related to Silicon Film Formation in a SiHCl ₃ -H ₂ System. <i>ECS Journal of Solid State Science and Technology</i> , 2016 , 5, P16-P20	2	3
105	Surface and gas phase reactions induced in a trichlorosilane-SiH _x system for silicon film deposition. <i>Surface and Coatings Technology</i> , 2015 , 272, 273-277	4.4	5
104	In Situ Cleaning Process of Silicon Carbide Epitaxial Reactor. <i>ECS Journal of Solid State Science and Technology</i> , 2015 , 4, P137-P140	2	14
103	Evaluation of Molecular Interaction between Organic Molecules Physisorbed on Silicon Native Oxide Surface in Dry and Humid Atmosphere. <i>ECS Journal of Solid State Science and Technology</i> , 2015 , 4, P86-P90	2	4
102	Cleaning Process for Using Chlorine Trifluoride Gas Silicon Carbide Chemical Vapor Deposition Reactor. <i>Materials Science Forum</i> , 2015 , 821-823, 125-128	0.4	3
101	Chlorine Trifluoride Gas Transport and Etching Rate Distribution in Silicon Carbide Dry Etcher. <i>Materials Science Forum</i> , 2015 , 821-823, 553-556	0.4	7
100	In Situ Method for Determining Combination of Organic Compounds Interacting with Each Other on Silicon Oxide Surface. <i>ECS Journal of Solid State Science and Technology</i> , 2015 , 4, P408-P414	2	1
99	Numerical evaluation of silicon epitaxial growth on a 450 mm diameter substrate. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2015 , 212, 1539-1543	1.6	2
98	In-situ observation of chemical vapor deposition using SiHCl ₃ and BCl ₃ gases. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2015 , 12, 953-957		2
97	By-Product Formation in a Trichlorosilane-Hydrogen System for Silicon Film Deposition. <i>ECS Journal of Solid State Science and Technology</i> , 2015 , 4, P16-P19	2	11
96	Metal Fluorides Produced Using Chlorine Trifluoride Gas. <i>Journal of Surface Engineered Materials and Advanced Technology</i> , 2015 , 05, 228-236	0.2	10
95	Low temperature amorphous silicon carbide thin film formation process on aluminum surface using monomethylsilane gas and trichlorosilane gas. <i>Journal of Crystal Growth</i> , 2014 , 401, 523-526	1.6	1
94	Precipitates Caused in Silicon Wafers by Prolonged High-Temperature Annealing in Nitrogen Atmosphere. <i>Materials Research Society Symposia Proceedings</i> , 2014 , 1591, 1		

93	Cleaning Process Applicable to Silicon Carbide Chemical Vapor Deposition Reactor. <i>ECS Journal of Solid State Science and Technology</i> , 2014 , 3, N3006-N3009	2	13
92	Off-Orientation Influence on C-Face (0001) 4H-SiC Surface Morphology Produced by Etching Using Chlorine Trifluoride Gas. <i>Materials Science Forum</i> , 2014 , 778-780, 734-737	0.4	
91	Precipitates formed in silicon wafers by prolonged high-temperature annealing in nitrogen atmosphere. <i>Japanese Journal of Applied Physics</i> , 2014 , 53, 05FJ05	1.4	2
90	Development of Silicon Carbide Dry Etcher Using Chlorine Trifluoride Gas. <i>Materials Science Forum</i> , 2014 , 778-780, 738-741	0.4	6
89	Room Temperature and Reduced Pressure Chemical Vapor Deposition of Silicon Carbide on Various Materials Surface. <i>Advances in Chemical Engineering and Science</i> , 2014 , 04, 389-395	0.4	1
88	Langasite crystal microbalance frequency behavior over wide gas phase conditions for chemical vapor deposition. <i>Surface and Coatings Technology</i> , 2013 , 230, 312-315	4.4	7
87	Silicon Chemical Vapor Deposition Process Using a Half-Inch Silicon Wafer for Minimal Manufacturing System. <i>Physics Procedia</i> , 2013 , 46, 230-238		6
86	Precipitates caused by prolonged high-temperature annealing in floating zone silicon wafer grown from Czochralski single-crystal rod. <i>Materials Science in Semiconductor Processing</i> , 2013 , 16, 923-927	4.3	3
85	Chemical vapor deposition of amorphous silicon carbide thin films on metal surfaces using monomethylsilane gas at low temperatures. <i>Surface and Coatings Technology</i> , 2013 , 217, 88-93	4.4	11
84	Crystalline Defects in Silicon Wafer Caused by Prolonged High-Temperature Annealing in Nitrogen Atmosphere. <i>Advanced Materials Research</i> , 2013 , 699, 445-449	0.5	
83	Amorphous Silicon Carbide Film Formation at Room Temperature by Monomethylsilane Gas. <i>Materials Science Forum</i> , 2013 , 740-742, 235-238	0.4	
82	Off-Orientation Influence on C-Face (0001) 4H-SiC Surface Morphology Produced by Etching Using Chlorine Trifluoride Gas. <i>ECS Journal of Solid State Science and Technology</i> , 2013 , 2, N3025-N3027	2	1
81	Surface Chemical Reaction Model of Silicon Dioxide Film Etching by Dilute Hydrogen Fluoride Using a Single Wafer Wet Etcher. <i>ECS Journal of Solid State Science and Technology</i> , 2013 , 2, P264-P267	2	8
80	Numerical calculation model of a single wafer wet etcher using a swinging nozzle. <i>Materials Science in Semiconductor Processing</i> , 2012 , 15, 543-548	4.3	8
79	Langasite Crystal Microbalance Used for In-Situ Monitoring of Amorphous Silicon Carbide Film Deposition. <i>ECS Journal of Solid State Science and Technology</i> , 2012 , 1, P62-P65	2	7
78	Room Temperature Process for Chemical Vapor Deposition of Amorphous Silicon Carbide Thin Film Using Monomethylsilane Gas. <i>Materials Research Society Symposia Proceedings</i> , 2012 , 1433, 83		
77	Density of Etch Pits on C-Face 4H-SiC Surface Produced by ClF ₃ Gas. <i>Materials Science Forum</i> , 2012 , 725, 49-52	0.4	7
76	Silicon Epitaxial Growth Rate and Transport Phenomena in a Vertical Stacked-Type Multi-Wafer Reactor. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 026701	1.4	

75	Density and Behavior of Etch Pits on C-Face 4H-SiC Surface Produced by ClF ₃ Gas. <i>Materials Science Forum</i> , 2012 , 717-720, 379-382	0.4	6
74	Concentration of Three Organic Compounds Influencing each other on Silicon Surface. <i>Solid State Phenomena</i> , 2012 , 187, 303-306	0.4	
73	Silicon Epitaxial Growth Rate and Transport Phenomena in a Vertical Stacked-Type Multi-Wafer Reactor. <i>Japanese Journal of Applied Physics</i> , 2012 , 51, 026701	1.4	
72	Mechanism of Silicon Carbide Film Deposition at Room Temperature Using Monomethylsilane Gas. <i>Journal of the Electrochemical Society</i> , 2011 , 158, H352	3.9	11
71	Low temperature SiC film deposition using trichlorosilane gas and monomethylsilane gas. <i>Journal of Nanoscience and Nanotechnology</i> , 2011 , 11, 8374-7	1.3	3
70	Room temperature process for chemical vapor deposition of amorphous silicon carbide thin film using monomethylsilane gas. <i>Surface and Coatings Technology</i> , 2011 , 206, 1503-1506	4.4	7
69	Silicon epitaxial growth process using trichlorosilane gas in a single-wafer high-speed substrate rotation reactor. <i>Journal of Crystal Growth</i> , 2011 , 327, 1-5	1.6	24
68	Langasite Crystal Microbalance for Development of Reactive Surface Preparation of Silicon Carbide Film Deposition from Monomethylsilane Gas. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 096505	1.4	4
67	Silicon Surface Morphology after Annealing in Ambient Hydrogen Containing a Trace Amount of Hydrogen Halide Gas. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 025701	1.4	
66	Etch Pits on 4H-SiC Surface Produced by ClF ₃ Gas. <i>Materials Science Forum</i> , 2011 , 679-680, 286-289	0.4	1
65	Water Motion over a Wafer Surface Rotating in a Single-Wafer Wet Cleaner. <i>ECS Transactions</i> , 2011 , 41, 279-286	1	2
64	Water Motion over a Wafer Surface Rotating in a Single-Wafer Wet Cleaner. <i>Journal of the Electrochemical Society</i> , 2011 , 158, H487	3.9	10
63	Langasite Crystal Microbalance for Development of Reactive Surface Preparation of Silicon Carbide Film Deposition from Monomethylsilane Gas. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 096505	1.4	2
62	Advance of Atomic Layer Deposition in Semiconductor Materials Manufacturing Process: Cleaning Technology for Thin Film Formation Reactor. <i>Journal of the Vacuum Society of Japan</i> , 2011 , 54, 97-104		
61	Silicon Surface Morphology after Annealing in Ambient Hydrogen Containing a Trace Amount of Hydrogen Halide Gas. <i>Japanese Journal of Applied Physics</i> , 2011 , 50, 025701	1.4	
60	Dominant Forces for Driving Bubbles in a Wet Cleaning Bath Using Megasonic Wave. <i>Journal of the Electrochemical Society</i> , 2010 , 157, H585	3.9	12
59	Molecular Interaction Radii and Rate Constants for Clarifying Organic Compound Physisorption on Silicon Surface. <i>Journal of the Electrochemical Society</i> , 2010 , 157, H1014	3.9	10
58	4H-SiC Surface Morphology Etched Using ClF ₃ Gas. <i>Materials Science Forum</i> , 2010 , 645-648, 787-790	0.4	9

57	Silicon carbide film deposition at low temperatures using monomethylsilane gas. <i>Surface and Coatings Technology</i> , 2010 , 204, 1432-1437	4.4	18
56	Temperature-Dependent Behavior of 4H-Silicon Carbide Surface Morphology Etched Using Chlorine Trifluoride Gas. <i>Journal of the Electrochemical Society</i> , 2009 , 156, H971	3.9	21
55	Hafnium Oxide Film Etching Using Hydrogen Chloride Gas. <i>Japanese Journal of Applied Physics</i> , 2009 , 48, 125503	1.4	2
54	Etching Rate of Silicon Dioxide Using Chlorine Trifluoride Gas. <i>Japanese Journal of Applied Physics</i> , 2009 , 48, 026504	1.4	8
53	Water and Bubble Motions Under Megasonic Wave in a Silicon Wafer Wet Cleaning Bath. <i>ECS Transactions</i> , 2009 , 25, 265-272	1	3
52	Etching Rate Behavior of 4H-Silicon Carbide Using Chlorine Trifluoride Gas. <i>ECS Transactions</i> , 2008 , 13, 39-52	1	8
51	Heat Transport and Temperature Gradient in Silicon-on-Insulator Wafer during Flash Lamp Annealing Process. <i>Japanese Journal of Applied Physics</i> , 2008 , 47, 6277-6281	1.4	2
50	4H Silicon Carbide Etching Using Chlorine Trifluoride Gas. <i>Materials Science Forum</i> , 2008 , 600-603, 655-658	1.4	10
49	Decarbonation and Pore Structural Change of Ca-Solid Reactant for CaO/CO ₂ Chemical Heat Pump. <i>Journal of Chemical Engineering of Japan</i> , 2008 , 41, 513-518	0.8	5
48	Polycrystalline silicon carbide film deposition using monomethylsilane and hydrogen chloride gases. <i>Journal of Crystal Growth</i> , 2007 , 300, 374-381	1.6	16
47	Water Motion in a Water Curtain Head for Cleaning a Large Glass Plate. <i>Japanese Journal of Applied Physics</i> , 2007 , 46, 838-842	1.4	
46	Determination of Etch Rate Behavior of 4H-SiC Using Chlorine Trifluoride Gas. <i>Japanese Journal of Applied Physics</i> , 2007 , 46, 7875-7879	1.4	22
45	Heat Transport Analysis for Flash Lamp Annealing. <i>Japanese Journal of Applied Physics</i> , 2007 , 46, 937-942	1.4	20
44	Physisorption and Desorption of Diethyl Phthalate and Isopropanol on a Silicon Surface. <i>Journal of the Electrochemical Society</i> , 2007 , 154, H1031	3.9	9
43	Carbonation/Decarbonation of Ca-Solid Reactant Derived from Natural Limestone for Thermal-Energy Storage and Temperature Upgrade. <i>Journal of Chemical Engineering of Japan</i> , 2007 , 40, 1270-1274	0.8	2
42	Small-Batch Reactor Development for Silicon Epitaxial Film Growth Based on Theory of Transport Phenomena. <i>ECS Transactions</i> , 2006 , 2, 21-32	1	2
41	Etch rate and surface morphology of polycrystalline silicon carbide using chlorine trifluoride gas. <i>Thin Solid Films</i> , 2006 , 514, 193-197	2.2	9
40	Dominant rate process of silicon surface etching by hydrogen chloride gas. <i>Thin Solid Films</i> , 2005 , 489, 104-110	2.2	31

39	Gas Velocity Influence on Silicon Surface Organic Contamination Evaluated Using Quartz Crystal Microbalance. <i>Journal of the Electrochemical Society</i> , 2005 , 152, G862	3.9	9
38	Silicon Carbide Etching Using Chlorine Trifluoride Gas. <i>Japanese Journal of Applied Physics</i> , 2005 , 44, 1376-1381	3.9	16
37	Quartz Crystal Microbalance for Silicon Surface Organic Contamination. <i>Journal of the Electrochemical Society</i> , 2005 , 152, G241	3.9	12
36	Highly Concentrated Ozone Gas for Preparing Wettable Polyimide Surface. <i>Japanese Journal of Applied Physics</i> , 2005 , 44, 5225-5230	1.4	2
35	Air Flow in Square Quartz Plate Spin Cleaner. <i>Japanese Journal of Applied Physics</i> , 2005 , 44, 8182-8185	1.4	2
34	Heat Balance Evaluation for Rapid Thermal Processing System Design. <i>Journal of the Electrochemical Society</i> , 2005 , 152, G924	3.9	5
33	Water Motion in Carrierless Wet Station. <i>Journal of the Electrochemical Society</i> , 2004 , 151, G814	3.9	9
32	Silicon Etch Rate Using Chlorine Trifluoride. <i>Journal of the Electrochemical Society</i> , 2004 , 151, G783	3.9	16
31	Formation mechanism of local thickness profile of silicon epitaxial film. <i>Journal of Crystal Growth</i> , 2004 , 266, 327-332	1.6	7
30	Time-Dependent Airborne Organic Contamination on Silicon Wafer Surface Stored in a Plastic Box. <i>Japanese Journal of Applied Physics</i> , 2003 , 42, 1575-1580	1.4	13
29	Airborne Organic Contamination Behavior on Silicon Wafer Surface. <i>Journal of the Electrochemical Society</i> , 2003 , 150, G148	3.9	18
28	High-Performance Silicon Etching Using Chlorine Trifluoride Gas. <i>Journal of the Electrochemical Society</i> , 2003 , 150, G461	3.9	15
27	Flatness Deterioration of Silicon Epitaxial Film Formed in a Horizontal Single-Wafer Epitaxial Reactor II. <i>Japanese Journal of Applied Physics</i> , 2002 , 41, 5692-5696	1.4	5
26	Model of boron incorporation into silicon epitaxial film in a B ₂ H ₆ /SiHCl ₃ /H ₂ system. <i>Journal of Crystal Growth</i> , 2001 , 222, 183-193	1.6	6
25	Hot-wall and cold-wall environments for silicon epitaxial film growth. <i>Journal of Crystal Growth</i> , 2001 , 223, 145-155	1.6	4
24	Design of a Rapid Thermal Processing System Using a Reflection-Resolved Ray Tracing Method. <i>Journal of the Electrochemical Society</i> , 2001 , 148, G543	3.9	8
23	Development of Evaluation Method for Organic Contamination on Silicon Wafer Surfaces. <i>Journal of the Electrochemical Society</i> , 2001 , 148, G644	3.9	18
22	Adsorption and Desorption Rate of Multicomponent Organic Species on Silicon Wafer Surface. <i>Journal of the Electrochemical Society</i> , 2001 , 148, G365	3.9	28

21	Nonempirical Design of Rapid Thermal Processing System. <i>Japanese Journal of Applied Physics</i> , 2001 , 40, 7123-7128	1.4	2
20	Flatness Deterioration of Silicon Epitaxial Film Formed Using Horizontal Single-Wafer Epitaxial Reactor. <i>Japanese Journal of Applied Physics</i> , 2001 , 40, 6041-6044	1.4	5
19	Instability of diborane gas in silicon epitaxial film growth. <i>Journal of Crystal Growth</i> , 2000 , 209, 807-815	1.6	11
18	Rate Theory of Multicomponent Adsorption of Organic Species on Silicon Wafer Surface. <i>Journal of the Electrochemical Society</i> , 2000 , 147, 2319	3.9	27
17	Thermal Conditions in Rapid Thermal Processing System Using Circular Infrared Lamp. <i>Journal of the Electrochemical Society</i> , 2000 , 147, 4660	3.9	8
16	CVD Material Processing. Numerical Calculations of Heat Profile using Circular Infrared Lamp Heating Furnace.. <i>Kagaku Kogaku Ronbunshu</i> , 2000 , 26, 785-791	0.4	2
15	Dominant Overall Chemical Reaction in a Chlorine Trifluoride-Silicon-Nitrogen System at Atmospheric Pressure. <i>Japanese Journal of Applied Physics</i> , 1999 , 38, 6466-6469	1.4	8
14	A Direct Approach for Evaluating the Thermal Condition of a Silicon Substrate under Infrared Rays and Specular Reflectors. <i>Journal of the Electrochemical Society</i> , 1999 , 146, 713-718	3.9	12
13	Chemical process of silicon epitaxial growth in a SiHCl ₃ -H ₂ system. <i>Journal of Crystal Growth</i> , 1999 , 207, 77-86	1.6	48
12	In situ cleaning method for silicon surface using hydrogen fluoride gas and hydrogen chloride gas in a hydrogen ambient. <i>Journal of Crystal Growth</i> , 1998 , 186, 104-112	1.6	11
11	Reaction of Hydrogen Fluoride Gas at High Temperatures with Silicon Oxide Film and Silicon Surface. <i>Japanese Journal of Applied Physics</i> , 1998 , 37, 6123-6127	1.4	12
10	Change in Microroughness of a Silicon Surface during In Situ Cleaning Using HF and HCl Gases. <i>Journal of the Electrochemical Society</i> , 1998 , 145, 4264-4271	3.9	6
9	Haze Generation on Silicon Surface Heated in Hydrogen Ambient at Atmospheric Pressure. <i>Journal of the Electrochemical Society</i> , 1997 , 144, 3261-3265	3.9	5
8	Computation Transport Phenomena in Chemical Engineering. Transport of Dopant Gas during Silicon Epitaxial Thin-Film Growth in a Horizontal Reactor.. <i>Kagaku Kogaku Ronbunshu</i> , 1997 , 23, 772-779 ^{0.4}	0.4	2
7	Nonlinear increase in silicon epitaxial growth rate in a SiHCl ₃ -H ₂ system under atmospheric pressure. <i>Journal of Crystal Growth</i> , 1997 , 182, 352-362	1.6	27
6	Effect of Transport Phenomena on Boron Concentration Profiles in Silicon Epitaxial Wafers. <i>Journal of the Electrochemical Society</i> , 1996 , 143, 677-682	3.9	3
5	Model on transport phenomena and epitaxial growth of silicon thin film in SiHCl ₃ -H ₂ system under atmospheric pressure. <i>Journal of Crystal Growth</i> , 1996 , 169, 61-72	1.6	75
4	Gas flow and heat transfer in a pancake chemical vapor deposition reactor. <i>Journal of Crystal Growth</i> , 1995 , 151, 375-383	1.6	8

3	Roughness of Silicon Surface Heated in Hydrogen Ambient. <i>Journal of the Electrochemical Society</i> , 1995 , 142, 3092-3098	3.9	29
2	Modeling of Epitaxial Silicon Thin-Film Growth on a Rotating Substrate in a Horizontal Single-Wafer Reactor. <i>Journal of the Electrochemical Society</i> , 1995 , 142, 4272-4278	3.9	30
1	Numerical Evaluation of Silicon-Thin Film Growth from SiHCl ₃ -H ₂ Gas Mixture in a Horizontal Chemical Vapor Deposition Reactor. <i>Japanese Journal of Applied Physics</i> , 1994 , 33, 1977-1985	1.4	15